

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE60P04SN uses advanced trench technology and design to provide excellent $R_{\text{DS(ON)}}$ with low gate charge .This device is well suited for use as a load switch or in PWM applications.

General Features

 \bullet V_{DS} =-60V,I_D =-4A

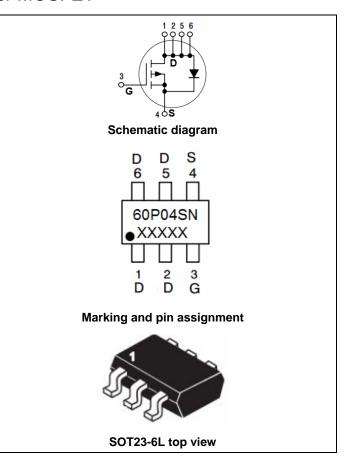
 $R_{DS(ON)}$ <120m Ω @ V_{GS} =-10V

 $R_{DS(ON)}$ <170m Ω @ V_{GS} =-4.5V

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Load switch
- PWM application



Package Marking and Ordering Information

D	evice Marking	Device	Device Package	Reel Size	Tape width	Quantity
	60P04SN	NCE60P04SN	SOT-23-6L	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_C=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	-4	А
Pulsed Drain Current	I _{DM}	-12	Α
Maximum Power Dissipation	P _D	1.5	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	83.3	°C/W
Thermal Resistance, Junction-to-Lead ^(Note 2)	$R_{ heta JL}$	75	°C/W

Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA -60		-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	iate-Body Leakage Current I _{GSS} V _{GS} =±20V,V _{DS} =0V		-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-1.0	-1.8	-2.5	V
Drain-Source On-State Resistance	Б	V _{GS} =-10V, I _D =-4A	-	106	120	mΩ
Diain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-3A	-	135	170	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-4A	-	10	-	S
Dynamic Characteristics (Note4)	·					
Input Capacitance	C _{lss}	\/ 20\/\/ 0\/	-	930	-	PF
Output Capacitance	C _{oss}	V_{DS} =-30V, V_{GS} =0V, F=1.0MHz	-	85	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVITZ	-	35	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	8	-	nS
Turn-on Rise Time	t _r	V_{DD} =-30V, R_L =7.5 Ω ,	-	4	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10 V , R_{G} =3 Ω	-	32	-	nS
Turn-Off Fall Time	t _f		-	7	-	nS
Total Gate Charge	Qg	V 00 L 4A	-	25	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =-30, I_{D} =-4A,	-	3	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =-10V	-	7	-	nC
Drain-Source Diode Characteristics	- 1		•			1
Diode Forward Voltage (Note 3)	V _{SD}	V_{GS} =0 V , I_{S} =-4 A	-		-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-4	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =- 4A	-	25		nS
Reverse Recovery Charge	Qrr	$di/dt = -100A/\mu s^{(Note3)}$	-	31		nC

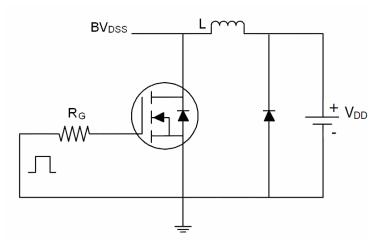
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. The value of R_{θJA} is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design. The R_{θJA} is the sum of the thermal impedence from junction to lead RθJL and lead to ambient.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production

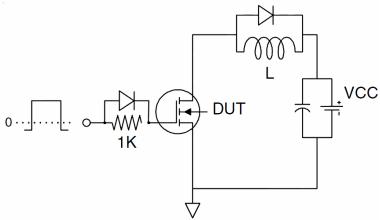


Test Circuit

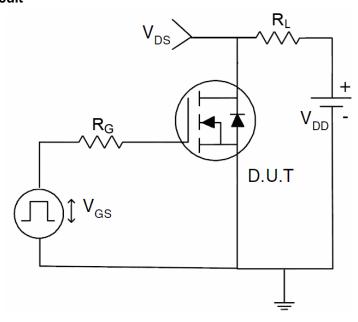
1) E_{AS} test Circuit



2) Gate charge test Circuit

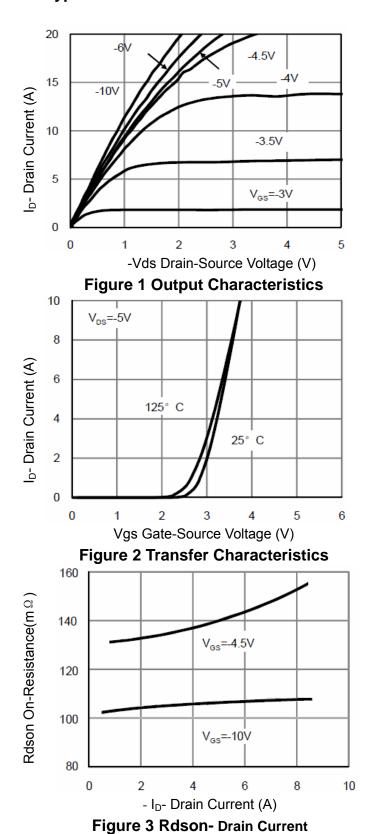


3) Switch Time Test Circuit

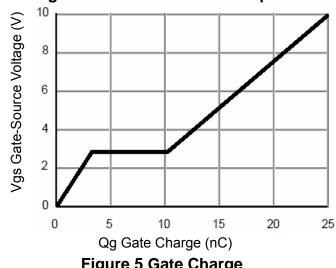




Typical Electrical and Thermal Characteristics (Curves)



2.00 Normalized On-Resistance 1.80 V_{GS}=-10V I_D=-4A 1.60 1.40 1.20 V_{GS}=-4.5V I_D=-3A 1.00 0.80 25 50 75 100 125 0 150 175 T_J-Junction Temperature(°C) **Figure 4 Rdson-Junction Temperature** 8



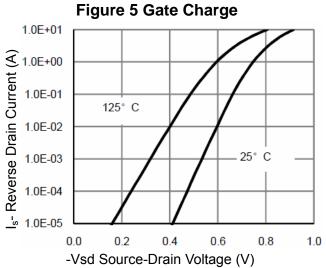


Figure 6 Source- Drain Diode Forward



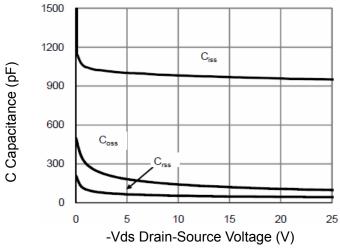


Figure 7 Capacitance vs Vds

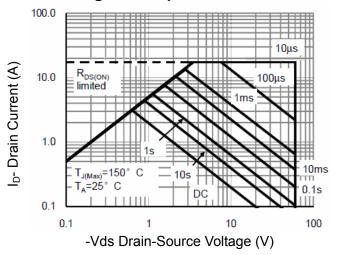


Figure 8 Safe Operation Area

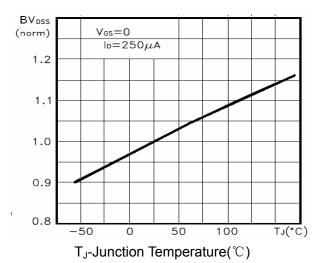


Figure 9 BV_{DSS} vs Junction Temperature

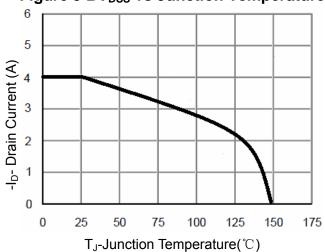


Figure 10 ID Current De-rating

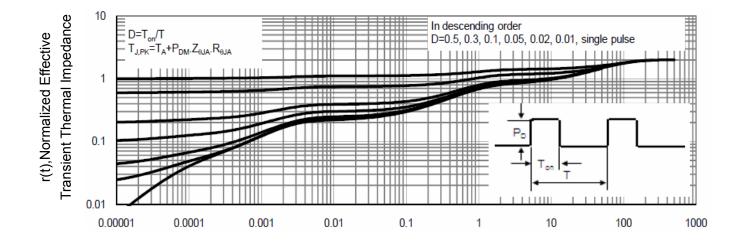
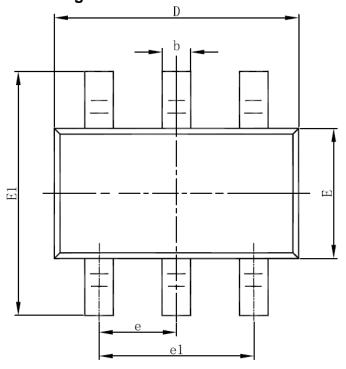


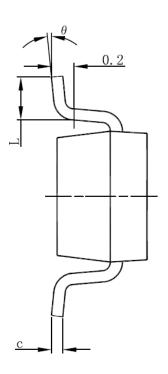
Figure 11 Normalized Maximum Transient Thermal Impedance

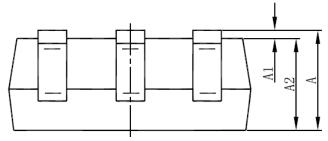
Square Wave Pluse Duration(sec)



SOT23-6L Package Information







Country of	Dimensions In Millimeters		Dimensions In Inches			
Symbol	Min	Max	Min	Max		
Α	1.050	1.250	0.041	0.049		
A1	0.000	0.100	0.000	0.004		
A2	1.050	1.150	0.041	0.045		
b	0.300	0.500	0.012	0.020		
С	0.100	0.200	0.004	0.008		
D	2.820	3.020	0.111	0.119		
E	1.500	1.700	0.059	0.067		
E1	2.650	2.950	0.104	0.116		
е	0.950	0.950(BSC)		0.037(BSC)		
e1	1.800	2.000	0.071	0.079		
L	0.300	0.600	0.012	0.024		
θ	0°	8°	0°	8°		

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NCE60P04SN

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